

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0236B.

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy .

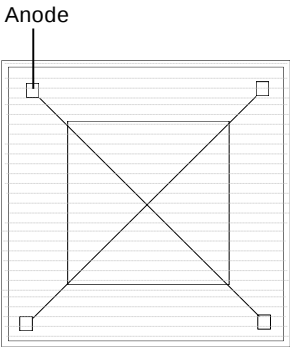
3. Size :

- 3-1. Chip size : 236 mils x 236 mils (6 mm x 6 mm).
- 3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
- 3-3. Active area : 223 mils x 223 mils (5.67 mm x 5.67 mm).
- 3-4. Bonding pad (Anode) : 8 mils x 8 mils (0.2 mm x 0.2 mm).
- 3-5. Pattern drawing : Refer to the attached drawing.

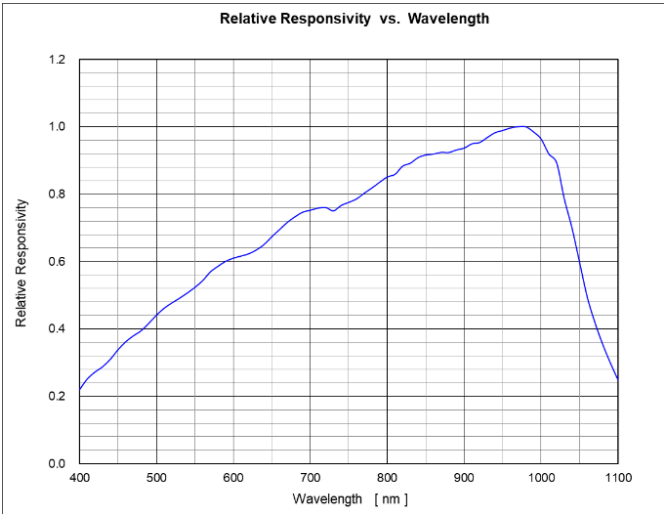
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			30	nA
*Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	30			V
*Forward Voltage	V_F	$I_F=20mA$ $E_e=0mW/cm^2$			1.2	V
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		320		μA
Total Capacitance	C_t	$V_R=5V$ $E_e=0mW/cm^2$ $f=1MHZ$		69		pF

*Based on 100% probing



5. Relative spectral responsivity



*Bare chip measured with integrating sphere, for reference only.